

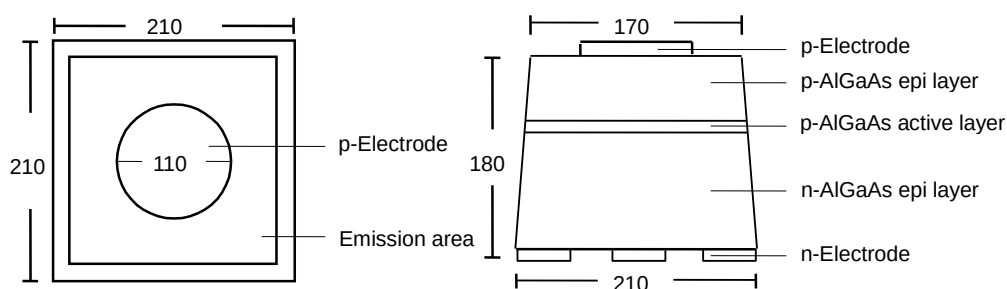
■ Features :

- AlGaAs/AlGaAs Wafer
- Very High Power
- High Speed
- High Performance
- Superior Thermal Stability

■ Typical Applications :

- IrDA
- Encoder
- Data Communication

■ Outline Dimensions : (Unit: μm)



■ Physical Structure :

Chip dimension	Chip size	210 μm x 210 μm
	Thickness	180 μm
	Emission area	170 μm
	Bonding pad	110 μm
Electrode	Top: P (anode)	Gold
	Backside: N (cathode)	Gold alloy
Surface condition	Frosted	

■ Electro-Optical Characteristics : ($T_a = 25^\circ\text{C}$)

Parameter	Symbol	Condition	Min.	Typ.	Max.	Unit
Forward Voltage	V_F	$I_F = 20 \text{ mA}$	-	1.44	1.60	V
		$I_F = 50 \text{ mA}$	-	1.56	1.80	
Reverse Voltage	V_R	$I_R = 10 \text{ uA}$	5	-	-	V
Wavelength	λ_P	$I_F = 50 \text{ mA}$	-	830	-	nm
Spectral width at half height	$\Delta\lambda$	$I_F = 50 \text{ mA}$	-	30	-	nm
Radiant Power	P_o	$I_F = 20 \text{ mA}$	1.00	1.50	-	mW
Rise / Fall Time	t_r / t_f	$I_F = 50 \text{ mA}$	-	25 / 15	35 / 35	ns

■ Typical Electro-Optical Characteristics Curve:

Fig 1. Forward Current vs. Forward Voltage

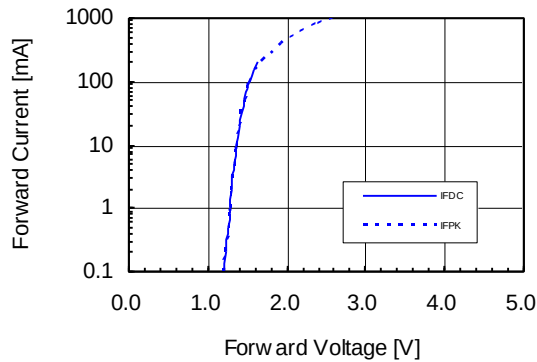


Fig 2. Relative Radiant Power vs. Wavelength

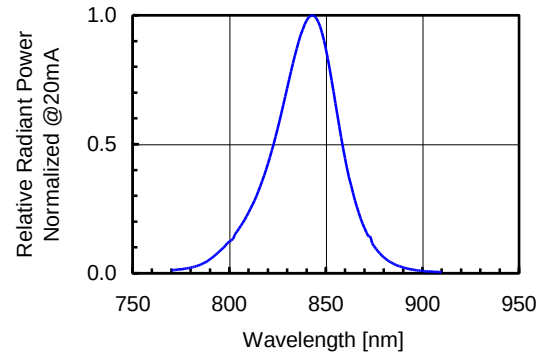
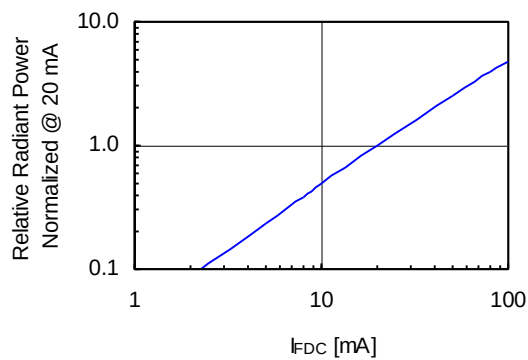
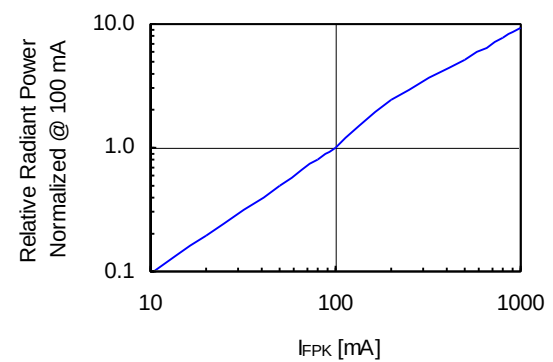
Fig 3. Relative Radiant Power
vs. Forward DC CurrentFig 4. Relative Radiant Power
vs. Forward Peak Current

Fig 5. Forward DC Voltage vs. Temperature

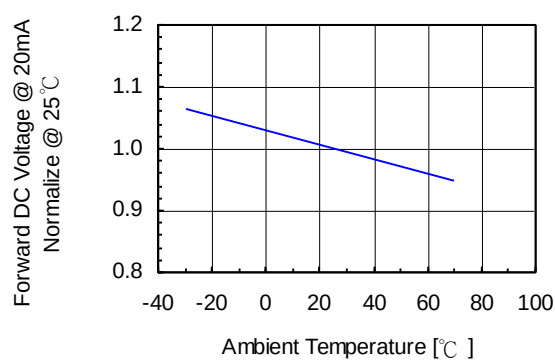


Fig 6. Relative Radiant Power vs. Temperature

